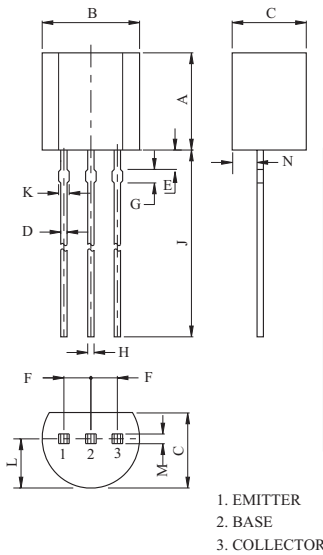
KN2907/A

EPITAXIAL PLANAR PNP TRANSISTOR

GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.

FEATURES

· Low Leakage Current
: I_{CEX}=-50nA(Max.) ; V_{CE}=-30V, V_{EB}=-0.5V.
· Low Saturation Voltage
: $V_{CE(sat)}$=-0.4V(Max.) ; I_C=-150mA, I_B=-15mA.
· Complementary to the KN2222/2222A.



DIM	MILLIMETERS
A	4.70 MAX
B	4.80 MAX
C	3.70 MAX
D	0.45
E	1.00
F	1.27
G	0.85
H	0.45
J	14.00±0.50
K	0.55 MAX
L	2.30
M	0.45 MAX
N	1.00

1. EMITTER
2. BASE
3. COLLECTOR

TO-92

MAXIMUM RATING (Ta=25℃)

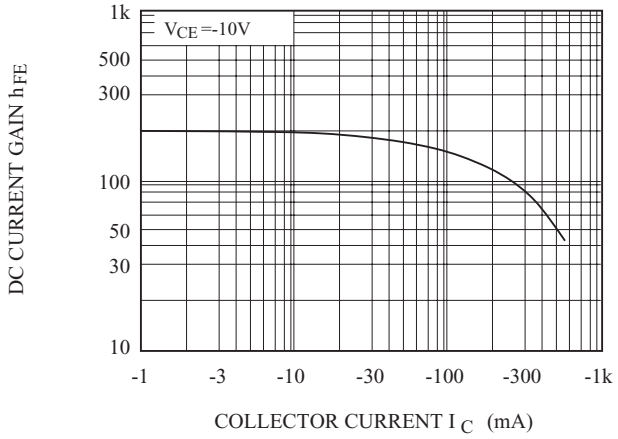
CHARACTERISTIC	SYMBOL	RATING		UNIT
		KN2907	KN2907A	
Collector-Base Voltage	V_{CBO}	-60		V
Collector-Emitter Voltage	V_{CEO}	-40	-60	V
Emitter-Base Voltage	V_{EBO}	-5		V
Collector Current	I_C	-600		mA
Collector Power Dissipation	P_C	625		mW
Junction Temperature	T_j	150		℃
Storage Temperature Range	T_{stg}	-55 ~ 150		℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

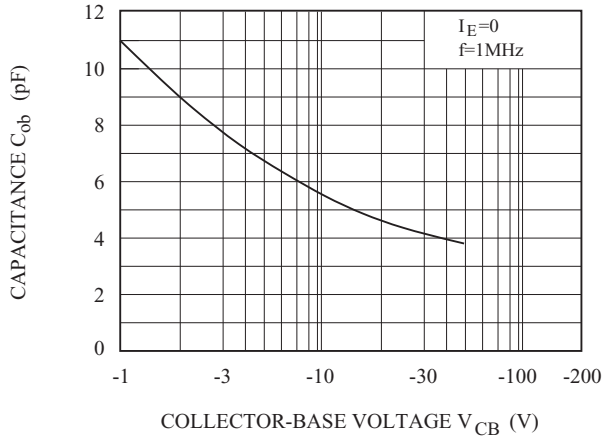
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CEX}	V_{CE}=-30V, V_{EB}=-0.5V	-	-	-50	nA
Collector Cut-off Current	KN2907	I_{CBO}	V_{CB}=-50V, I_E=0	-	-	-20	nA
	KN2907A			-	-	-10	
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	I_C=-10μA, I_E=0	-60	-	-	V
Collector-Emitter Breakdown Voltage *	KN2907	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-40	-	-	V
	KN2907A			-60	-	-	
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	I_E=-10μA, I_C=0	-5	-	-	V
DC Current Gain	KN2907	h_{FE}(1)	I_C=-0.1mA, V_{CE}=-10V	35	-	-	
	KN2907A			75	-	-	
	KN2907	h_{FE}(2)	I_C=-1.0mA, V_{CE}=-10V	50	-	-	
	KN2907A			100	-	-	
	KN2907	h_{FE}(3)	I_C=-10mA, V_{CE}=-10V	75	-	-	
	KN2907A			100	-	-	
	KN2907	h_{FE}(4) *	I_C=-150mA, V_{CE}=-10V	100	-	300	
	KN2907A						
	KN2907	h_{FE}(5) *	I_C=-500mA, V_{CE}=-10V	30	-	-	
	KN2907A			50	-	-	
Collector-Emitter Saturation Voltage *		$V_{CE(sat)}$1	I_C=-150mA, I_B=-15mA	-	-	-0.4	V
		$V_{CE(sat)}$2	I_C=-500mA, I_B=-50mA	-	-	-1.6	
Base-Emitter Saturation Voltage *		$V_{BE(sat)}$1	I_C=-150mA, I_B=-15mA	-	-	-1.3	V
		$V_{BE(sat)}$2	I_C=-500mA, I_B=-50mA	-	-	-2.6	
Transition Frequency		f_T	V_{CE}=-20V, I_C=-50mA, f=100MHz	200	-	-	MHz
Collector Output Capacitance		C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	-	8	pF

* Pulse Test : Pulse Width ≦300μS, Duty Cycle ≦2%.

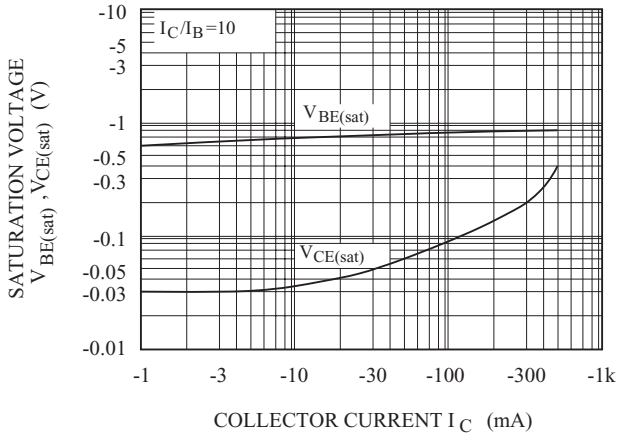
h_{FE} - I_C



C_{ob} - V_{CB}



$V_{BE(sat)}$,$V_{CE(sat)}$ - I_C



Pc - Ta